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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

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2 0 0 0 0 0	
Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	64
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	20K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 17x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	80-LQFP
Supplier Device Package	80-LFQFP (12x12)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f100mjafb-x0

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

Table 1-1. List of Ordering Part Numbers

Dia	Destaurs	Data flash	E data a f	(3/12)
Pin count	Package	Data flash	Fields of Application	Ordering Part Number
36 pins	36-pin plastic WFLGA (4 × 4 mm, 0.5 mm pitch)	Mounted	A	R5F100CAALA#U0, R5F100CCALA#U0, R5F100CDALA#U0, R5F100CEALA#U0, R5F100CFALA#U0, R5F100CGALA#U0 R5F100CAALA#W0, R5F100CCALA#W0, R5F100CDALA#W0, R5F100CEALA#W0, R5F100CFALA#W0, R5F100CGALA#W0
			G	R5F100CAGLA#U0, R5F100CCGLA#U0, R5F100CDGLA#U0, R5F100CEGLA#U0, R5F100CFGLA#U0, R5F100CGGLA#U0 R5F100CAGLA#W0, R5F100CCGLA#W0, R5F100CDGLA#W0, R5F100CEGLA#W0, R5F100CFGLA#W0, R5F100CGGLA#W0
		Not mounted	A	R5F101CAALA#U0, R5F101CCALA#U0, R5F101CDALA#U0, R5F101CEALA#U0, R5F101CFALA#U0, R5F101CGALA#U0 R5F101CAALA#W0, R5F101CCALA#W0, R5F101CDALA#W0, R5F101CEALA#W0, R5F101CFALA#W0, R5F101CGALA#W0
40 pins	40-pin plastic HWQFN (6 × 6 mm, 0.5 mm pitch)	Mounted	A	R5F100EAANA#U0, R5F100ECANA#U0, R5F100EDANA#U0, R5F100EEANA#U0, R5F100EFANA#U0, R5F100EGANA#U0, R5F100EHANA#U0 R5F100EAANA#W0, R5F100ECANA#W0, R5F100EDANA#W0, R5F100EEANA#W0, R5F100EFANA#W0, R5F100EGANA#W0, R5F100EHANA#W0
			D	R5F100EADNA#U0, R5F100ECDNA#U0, R5F100EDDNA#U0, R5F100EEDNA#U0, R5F100EFDNA#U0, R5F100EGDNA#U0, R5F100EHDNA#U0 R5F100EADNA#W0, R5F100ECDNA#W0, R5F100EDDNA#W0, R5F100EEDNA#W0, R5F100EFDNA#W0, R5F100EGDNA#W0, R5F100EHDNA#W0
			G	R5F100EAGNA#U0, R5F100ECGNA#U0, R5F100EDGNA#U0, R5F100EEGNA#U0, R5F100EFGNA#U0, R5F100EGGNA#U0, R5F100EHGNA#U0 R5F100EAGNA#W0, R5F100ECGNA#W0, R5F100EDGNA#W0, R5F100EEGNA#W0, R5F100EFGNA#W0, R5F100EGGNA#W0, R5F100EHGNA#W0
		Not mounted	A	R5F101EAANA#U0, R5F101ECANA#U0, R5F101EDANA#U0, R5F101EEANA#U0, R5F101EFANA#U0, R5F101EGANA#U0, R5F101EHANA#U0 R5F101EAANA#W0, R5F101ECANA#W0, R5F101EDANA#W0, R5F101EEANA#W0, R5F101EFANA#W0, R5F101EGANA#W0, R5F101EHANA#W0
			D	R5F101EADNA#U0, R5F101ECDNA#U0, R5F101EDDNA#U0, R5F101EEDNA#U0, R5F101EFDNA#U0, R5F101EGDNA#U0, R5F101EHDNA#U0 R5F101EADNA#W0, R5F101ECDNA#W0, R5F101EDDNA#W0, R5F101EEDNA#W0, R5F101EFDNA#W0, R5F101EGDNA#W0, R5F101EHDNA#W0

Note For the fields of application, refer to Figure 1-1 Part Number, Memory Size, and Package of RL78/G13.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.



Table 1-1.	List of Ordering Part Nu	umbers
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				(12/12)
Pin count	Package	Data flash	Fields of Application ^{Note}	Ordering Part Number
128 pins	128-pin plastic LFQFP (14 × 20 mm, 0.5 mm pitch)	Mounted	A	R5F100SHAFB#V0, R5F100SJAFB#V0, R5F100SKAFB#V0, R5F100SLAFB#V0 R5F100SHAFB#X0, R5F100SJAFB#X0, R5F100SKAFB#X0, R5F100SLAFB#X0 R5F100SHDFB#V0, R5F100SJDFB#V0, R5F100SKDFB#V0, R5F100SLDFB#V0 R5F100SKDFB#X0, R5F100SJDFB#X0, R5F100SKDFB#X0, R5F100SLDFB#X0
		Not mounted	D	R5F101SHAFB#V0, R5F101SJAFB#V0, R5F101SKAFB#V0, R5F101SLAFB#V0 R5F101SHAFB#X0, R5F101SJAFB#X0, R5F101SKAFB#X0, R5F101SLAFB#X0 R5F101SHDFB#V0, R5F101SJDFB#V0, R5F101SKDFB#V0, R5F101SLDFB#V0 R5F101SHDFB#X0, R5F101SLDFB#X0, R5F101SKDFB#X0, R5F101SLDFB#X0

Note For the fields of application, refer to Figure 1-1 Part Number, Memory Size, and Package of RL78/G13.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.



1.3 Pin Configuration (Top View)

1.3.1 20-pin products

• 20-pin plastic LSSOP (7.62 mm (300), 0.65 mm pitch)



Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remark For pin identification, see 1.4 Pin Identification.



1.3.14 128-pin products

• 128-pin plastic LFQFP (14 × 20 mm, 0.5 mm pitch)



Cautions 1. Make EVsso, EVss1 pins the same potential as Vss pin.

- 2. Make VDD pin the potential that is higher than EVDD0, EVDD1 pins (EVDD0 = EVDD1).
- 3. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

- 2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the VDD, EVDD0 and EVDD1 pins and connect the Vss, EVss0 and EVss1 pins to separate ground lines.
- **3.** Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.



Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, low ^{Note 1}	Iol1	Per pin for P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147				20.0 Note 2	mA
		Per pin for P60 to P63				15.0 Note 2	mA
		Total of P00 to P04, P07, P32 to	$4.0~V \leq EV_{\text{DD0}} \leq 5.5~V$			70.0	mA
		P37,	$2.7~V \leq EV_{\text{DD0}} < 4.0~V$			15.0	mA
		P125 to P127, P130, P140 to P145	$1.8~V \leq EV_{\text{DD0}} < 2.7~V$			9.0	mA
			$1.6~V \leq EV_{\text{DD0}} < 1.8~V$			4.5	mA
		Total of P05, P06, P10 to P17, P30,	$4.0~V \leq EV_{\text{DD0}} \leq 5.5~V$			80.0	mA
			$2.7~V \leq EV_{\text{DD0}} < 4.0~V$			35.0	mA
		P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146,	$1.8~V \leq EV_{\text{DD0}} < 2.7~V$			20.0	mA
		P147 (When duty $\leq 70\%^{\text{Note 3}}$)	$1.6 \text{ V} \leq \text{EV}_{\text{DD0}} < 1.8 \text{ V}$			10.0	mA
		Total of all pins (When duty $\leq 70\%^{\text{Note 3}}$)				150.0	mA
	Iol2	Per pin for P20 to P27, P150 to P156				0.4 Note 2	mA
		Total of all pins (When duty $\leq 70\%^{Note 3}$)	$1.6~V \leq V_{\text{DD}} \leq 5.5~V$			5.0	mA

$(T_A = -40 \text{ to } +85^{\circ}C, 1.6 \text{ V} \le EV_{DD0} = EV_{DD1} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = EV_{SS0} = EV_{SS1} = 0 \text{ V})$ (2/5)

- **Notes 1**. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the EVsso, EVss1 and Vss pin.
 - 2. However, do not exceed the total current value.
 - **3.** Specification under conditions where the duty factor \leq 70%.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins = $(I_{OL} \times 0.7)/(n \times 0.01)$

<Example> Where n = 80% and $I_{OL} = 10.0 \text{ mA}$

Total output current of pins = $(10.0 \times 0.7)/(80 \times 0.01) \approx 8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (1/3)

Parameter	Symbol		Conditions	HS (hig	h-speed Mode	LS (low		`	-voltage Mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t ксү1	tксү1 ≥ 4/fc∟к	$\begin{array}{l} 4.0 \ V \leq EV_{\text{DD0}} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V, \\ C_b = 30 \ pF, \ R_b = 1.4 \ k\Omega \end{array}$	300		1150		1150		ns
			$\begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	500		1150		1150		ns
			$\begin{array}{l} 1.8 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V^{\text{Note}}, \end{array}$	1150		1150		1150		ns
SCKp high-level width	tкнı	$\label{eq:constraint} \begin{array}{l} 2.7 \ V \leq V_b \leq 4.0 \ V, \\ \\ C_b = 30 \ pF, \ R_b = 1.4 \ k\Omega \end{array}$		tксү1/2 – 75		tксү1/2 – 75		tксү1/2 – 75		ns
				tксү1/2 – 170		tксү1/2 – 170		tксү1/2 – 170		ns
		$1.8 V \le EV_{DI}$ $1.6 V \le V_b \le C_b = 30 \text{ pF},$	2.0 V ^{Note} ,	tксү1/2 – 458		tксү1/2 – 458		tксү1/2 – 458		ns
SCKp low-level width	tĸ∟ı	$4.0 \text{ V} \leq \text{EV}_{\text{DI}}$ $2.7 \text{ V} \leq \text{V}_{\text{b}} \leq$ $C_{\text{b}} = 30 \text{ pF},$	∞ ≤ 5.5 V, 4.0 V,	tксү1/2 – 12		tксү1/2 – 50		tксү1/2 – 50		ns
		$\begin{array}{l} 2.7 \ V \leq EV_{DI} \\ 2.3 \ V \leq V_b \leq \end{array}$	₀₀ < 4.0 V, 2.7 V,	tксү1/2 – 18		tксү1/2 – 50		tксү1/2 – 50		ns
		$\label{eq:cb} \begin{split} &C_{\rm b} = 30 \ p F, \\ &1.8 \ V \leq E V_{\rm DI} \\ &1.6 \ V \leq V_{\rm b} \leq \\ &C_{\rm b} = 30 \ p F, \end{split}$	⁰⁰ < 3.3 V, 2.0 V ^{Note} ,	tксү1/2 – 50		tксү1/2 – 50		tксү1/2 – 50		ns

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

Note Use it with $EV_{DD0} \ge V_b$.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (When 20- to 52-pin products)/EVDD tolerance (When 64- to 128-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed two pages after the next page.)



(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (2/3)

Parameter	Symbol	Conditions		h-speed Mode	``	/-speed Mode		-voltage Mode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SIp setup time (to SCKp↑) ^{Note 1}	tsikı	$\begin{array}{l} 4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V, \end{array}$	81		479		479		ns
		$C_b = 30 \text{ pF}, \text{ R}_b = 1.4 \text{ k}\Omega$							
		$\begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \end{array}$	177		479		479		ns
		$C_b=30 \text{ pF}, \text{R}_b=2.7 \text{k}\Omega$							
		$\label{eq:VDD} \begin{split} 1.8 \ V &\leq EV_{\text{DD0}} < 3.3 \ V, \\ 1.6 \ V &\leq V_{\text{b}} \leq 2.0 \ V^{\text{Note 2}}, \end{split}$	479		479		479		ns
		C_b = 30 pF, R_b = 5.5 k Ω							
SIp hold time (from SCKp↑) ^{Note 1}	tksi1	$\begin{array}{l} 4.0 \ V \leq EV_{\text{DD0}} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V, \end{array}$	19		19		19		ns
		C_b = 30 pF, R_b = 1.4 k Ω							
		$\begin{array}{l} 2.7 \ V \leq EV_{\text{DD0}} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \end{array}$	19		19		19		ns
		C_b = 30 pF, R_b = 2.7 k Ω							
		$\label{eq:VDD} \begin{split} 1.8 \ V &\leq EV_{\text{DD0}} < 3.3 \ V, \\ 1.6 \ V &\leq V_b \leq 2.0 \ V^{\text{Note 2}}, \end{split}$	19		19		19		ns
		C_b = 30 pF, R_b = 5.5 k Ω							
Delay time from SCKp↓ to	tkso1	$\begin{array}{l} 4.0 \ V \leq EV_{\text{DD0}} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V, \end{array}$		100		100		100	ns
SOp output Note 1		C_b = 30 pF, R_b = 1.4 k Ω							
		$\begin{array}{l} 2.7 \ V \leq EV_{\text{DD0}} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \end{array}$		195		195		195	ns
		C_b = 30 pF, R_b = 2.7 k Ω							
		$\label{eq:VDD} \begin{split} 1.8 \ V &\leq EV_{\text{DD0}} < 3.3 \ V, \\ 1.6 \ V &\leq V_b \leq 2.0 \ V^{\text{Note 2}}, \end{split}$		483		483		483	ns
		C_b = 30 pF, R_b = 5.5 k Ω							

		5 5 V Voo - EVo	$ = EV_{oot} = 0.V$
$T_{A} = -40$ to +85°C,		j.j v, vss = ⊑vs	$s_0 = \Box v s s_1 = U v $

Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

2. Use it with $EV_{DD0} \ge V_b$.

(Remarks are listed on the page after the next page.)



Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (When 20- to 52-pin products)/EVDD tolerance (When 64- to 128-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

CSI mode connection diagram (during communication at different potential)



- **Remarks 1.** R_b[Ω]:Communication line (SOp) pull-up resistance, C_b[F]: Communication line (SOp) load capacitance, V_b[V]: Communication line voltage
 - 2. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)
 - 3. fмск: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13))
 - **4.** CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.



(3) When reference voltage (+) = VDD (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = Vss (ADREFM = 0), target pin : ANI0 to ANI14, ANI16 to ANI26, internal reference voltage, and temperature sensor output voltage

$(T_{A} = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \leq \text{EV}_{\text{DD}} = \text{EV}_{\text{DD}} \leq 5.5 \text{ V}, \text{ Vss} = \text{EV}_{\text{SS}} = \text{EV}_{\text{SS}} = 0 \text{ V}, \text{ Reference voltage (+)} = \text{V}_{\text{DD}}, \text{ V}_{\text{DD}} = 0 \text{ V}, \text{ Reference voltage (+)} = 0 \text{ V}, Reference voltage (+)$
Reference voltage (-) = Vss)

Parameter	Symbol	Conditio	ns	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution	$1.8~V \le V \text{DD} \le 5.5~V$		1.2	±7.0	LSB
			$\frac{1.6~V \leq V\text{DD} \leq 5.5~V}{_{\text{Note 3}}}$		1.2	±10.5	LSB
Conversion time	t CONV	10-bit resolution	$3.6~V \le V \text{DD} \le 5.5~V$	2.125		39	μs
		Target pin: ANI0 to ANI14,	$2.7~V \leq V \text{DD} \leq 5.5~V$	3.1875		39	μs
		ANI16 to ANI26	$1.8~V \le V \text{DD} \le 5.5~V$	17		39	μs
			$1.6~V \leq V \text{DD} \leq 5.5~V$	57		95	μs
Conversion time	tconv	10-bit resolution	$3.6~V \leq V \text{DD} \leq 5.5~V$	2.375		39	μs
		Target pin: Internal	$2.7~V \leq V \text{DD} \leq 5.5~V$	3.5625		39	μs
	reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$2.4~V \leq V \text{DD} \leq 5.5~V$	17		39	μs	
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution	$1.8~V \leq V \text{DD} \leq 5.5~V$			±0.60	%FSR
			$1.6~V \leq V \text{DD} \leq 5.5~V$ Note 3			±0.85	%FSR
Full-scale error ^{Notes 1, 2}	Efs	10-bit resolution	$1.8~V \le V \text{DD} \le 5.5~V$			±0.60	%FSR
			$\frac{1.6~V \leq V\text{DD} \leq 5.5~V}{_{\text{Note 3}}}$			±0.85	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution	$1.8~V \leq V \text{DD} \leq 5.5~V$			±4.0	LSB
			$\frac{1.6~V \leq V \text{DD} \leq 5.5~V}{_{\text{Note 3}}}$			±6.5	LSB
Differential linearity error Note 1	DLE	10-bit resolution	$1.8~V \leq V \text{DD} \leq 5.5~V$			±2.0	LSB
			$\frac{1.6~V \leq V\text{DD} \leq 5.5~V}{_{\text{Note 3}}}$			±2.5	LSB
Analog input voltage	VAIN	ANI0 to ANI14	•	0		Vdd	V
		ANI16 to ANI26		0		EVDD0	V
	Internal reference voltage (2.4 V \leq VDD \leq 5.5 V, HS (hig		gh-speed main) mode)		VBGR Note 4		V
		Temperature sensor output (2.4 V \leq V _{DD} \leq 5.5 V, HS (high	•	VTMPS25 ^{Note 4}		1	V

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- 3. When the conversion time is set to 57 μs (min.) and 95 μs (max.).
- 4. Refer to 2.6.2 Temperature sensor/internal reference voltage characteristics.



2.6.5 Power supply voltage rising slope characteristics

$(T_A = -40 \text{ to } +85^{\circ}C, V_{SS} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	SVDD				54	V/ms

Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until V_{DD} reaches the operating voltage range shown in 2.4 AC Characteristics.

2.7 RAM Data Retention Characteristics

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	VDDDR		1.46 ^{Note}		5.5	V

Note This depends on the POR detection voltage. For a falling voltage, data in RAM are retained until the voltage reaches the level that triggers a POR reset but not once it reaches the level at which a POR reset is generated.





3.3 DC Characteristics

3.3.1 Pin characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$ (1/5)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high ^{∾te 1}	Іон1	Per pin for P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	$2.4~V \leq EV_{DD0} \leq 5.5~V$			-3.0 Note 2	mA
		Total of P00 to P04, P07, P32 to P37,	$4.0~V \leq EV_{\text{DD0}} \leq 5.5~V$			-30.0	mA
		P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145	$2.7~V \leq EV_{\text{DD0}} < 4.0~V$			-10.0	mA
			$2.4~V \leq EV_{\text{DD0}} < 2.7~V$			-5.0	mA
		Total of P05, P06, P10 to P17, P30, P31,				-30.0	mA
		P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to	$2.7~V \leq EV_{\text{DD0}} < 4.0~V$			-19.0	mA
		P117, P146, P147 (When duty $\leq 70\%^{\text{Note 3}}$)	$2.4~V \leq EV_{DD0} < 2.7~V$			-10.0	mA
		Total of all pins (When duty ≤ 70% ^{№te 3})	$2.4~V \leq EV_{\text{DD0}} \leq 5.5~V$			-60.0	mA
	Іон2	Per pin for P20 to P27, P150 to P156	2,4 V \leq V_{DD} \leq 5.5 V			-0.1 ^{Note 2}	mA
		Total of all pins (When duty $\leq 70\%^{Note 3}$)	$2.4~V \leq V_{\text{DD}} \leq 5.5~V$			-1.5	mA

- **Notes 1**. Value of current at which the device operation is guaranteed even if the current flows from the EV_{DD0}, EV_{DD1}, V_{DD} pins to an output pin.
 - 2. Do not exceed the total current value.
 - 3. Specification under conditions where the duty factor ≤ 70%. The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).
 - Total output current of pins = $(I_{OH} \times 0.7)/(n \times 0.01)$
 - <Example> Where n = 80% and $I_{OH} = -10.0 \text{ mA}$
 - Total output current of pins = $(-10.0 \times 0.7)/(80 \times 0.01) \cong -8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

- Caution P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 do not output high level in N-ch open-drain mode.
- **Remark** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



3.5.2 Serial interface IICA

Parameter	Symbol	Symbol Conditions		HS (high-speed main) Mode			
			Standard Fast Mode Mode				
			MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fsc∟	Fast mode: fclk ≥ 3.5 MHz	-	-	0	400	kHz
		Standard mode: fclk ≥ 1 MHz	0	100	-	_	kHz
Setup time of restart condition	tsu:sta		4.7		0.6		μS
Hold time ^{Note 1}	thd:sta		4.0		0.6		μS
Hold time when SCLA0 = "L"	t∟ow		4.7		1.3		μs
Hold time when SCLA0 = "H"	tніgн		4.0		0.6		μs
Data setup time (reception)	tsu:dat		250		100		ns
Data hold time (transmission)Note 2	thd:dat		0	3.45	0	0.9	μS
Setup time of stop condition	tsu:sto		4.0		0.6		μs
Bus-free time	t BUF		4.7		1.3		μs

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{ Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

<R>

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

2. The maximum value (MAX.) of the:DAT is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

Caution The values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (IOH1, IOL1, VOH1, VOL1) must satisfy the values in the redirect destination.

Remark The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

 $\begin{array}{ll} \mbox{Standard mode:} & C_b = 400 \mbox{ pF}, \mbox{ } R_b = 2.7 \mbox{ } k\Omega \\ \mbox{Fast mode:} & C_b = 320 \mbox{ pF}, \mbox{ } R_b = 1.1 \mbox{ } k\Omega \\ \end{array}$

IICA serial transfer timing







3.6 Analog Characteristics

3.6.1 A/D converter characteristics

Classification of A/D converter characteristics

		Reference Voltage	
	Reference voltage (+) = AVREFP	Reference voltage (+) = VDD	Reference voltage (+) = VBGR
Input channel	Reference voltage (-) = AVREFM	Reference voltage (-) = Vss	Reference voltage (-) = AVREFM
ANI0 to ANI14	Refer to 3.6.1 (1).	Refer to 3.6.1 (3) .	Refer to 3.6.1 (4).
ANI16 to ANI26	Refer to 3.6.1 (2).		
Internal reference voltage	Refer to 3.6.1 (1) .		-
Temperature sensor output			
voltage			

(1) When reference voltage (+) = AV_{REFP}/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AV_{REFM}/ANI1 (ADREFM = 1), target pin : ANI2 to ANI14, internal reference voltage, and temperature sensor output voltage

(T_A = -40 to +105°C, 2.4 V \leq AV_{REFP} \leq V_{DD} \leq 5.5 V, V_{SS} = 0 V, Reference voltage (+) = AV_{REFP}, Reference voltage (-) = AV_{REFM} = 0 V)

Parameter	Symbol	Condition	ns	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}	$2.4~V \leq AV_{\text{REFP}} \leq 5.5~V$		1.2	±3.5	LSB
Conversion time	t CONV	10-bit resolution	$3.6~V \le V \text{DD} \le 5.5~V$	2.125		39	μS
		Target pin: ANI2 to ANI14	$2.7~V \leq V_{DD} \leq 5.5~V$	3.1875		39	μs
			$2.4~V \leq V_{DD} \leq 5.5~V$	17		39	μs
		10-bit resolution	$3.6~V \leq V \text{DD} \leq 5.5~V$	2.375		39	μS
		Target pin: Internal reference	$2.7~V \le V \text{DD} \le 5.5~V$	3.5625		39	μs
		voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$2.4~V \le V \text{dd} \le 5.5~V$	17		39	μs
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}	$\begin{array}{l} 2.4 \hspace{.1in} V \leq AV_{\text{REFP}} \leq 5.5 \\ V \end{array}$			±0.25	%FSR
Full-scale error ^{Notes 1, 2}	Efs	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}	$\begin{array}{l} 2.4 \hspace{.1cm} V \leq AV_{\text{REFP}} \leq 5.5 \\ V \end{array}$			±0.25	%FSR
Integral linearity error	ILE	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}	$\begin{array}{l} 2.4 \hspace{.1cm} V \hspace{.1cm} \leq \hspace{.1cm} AV_{\text{REFP}} \hspace{.1cm} \leq \hspace{.1cm} 5.5 \\ V \end{array}$			±2.5	LSB
Differential linearity error	DLE	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}	$\begin{array}{l} 2.4 \hspace{.1cm} V \leq AV_{\text{REFP}} \leq 5.5 \\ V \end{array}$			±1.5	LSB
Analog input voltage	VAIN	ANI2 to ANI14		0		AVREFP	V
		Internal reference voltage output (2.4 V \leq VDD \leq 5.5 V, HS (high-speed main) mode)			VBGR Note 4		V
		Temperature sensor output vo (2.4 V \leq VDD \leq 5.5 V, HS (high		VTMPS25 Note	4	V	

(Notes are listed on the next page.)



- **Notes 1.** Excludes quantization error ($\pm 1/2$ LSB).
 - 2. This value is indicated as a ratio (%FSR) to the full-scale value.
 - $\label{eq:scalar} \begin{array}{l} \textbf{3. When } AV_{\text{REFP}} < V_{\text{DD}} \text{, the MAX. values are as follows.} \\ \text{Overall error: } Add \pm 1.0 \ \text{LSB} \ \text{to the MAX. value when } AV_{\text{REFP}} = V_{\text{DD}} \text{.} \\ \text{Zero-scale error/Full-scale error: } Add \pm 0.05\%\text{FSR} \ \text{to the MAX. value when } AV_{\text{REFP}} = V_{\text{DD}} \text{.} \\ \text{Integral linearity error/ Differential linearity error: } Add \pm 0.5 \ \text{LSB} \ \text{to the MAX. value when } AV_{\text{REFP}} = V_{\text{DD}} \text{.} \\ \end{array}$
 - 4. Refer to 3.6.2 Temperature sensor/internal reference voltage characteristics.



3.6.4 LVD circuit characteristics

LVD Detection Voltage of Reset Mode and Interrupt Mode

(TA = -40 to +105°C, VPDR \leq VDD \leq 5.5 V, Vss = 0 V)

	Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection	Supply voltage level	VLVD0	Power supply rise time	3.90	4.06	4.22	V
voltage			Power supply fall time	3.83	3.98	4.13	V
		VLVD1	Power supply rise time	3.60	3.75	3.90	V
			Power supply fall time	3.53	3.67	3.81	V
		VLVD2	Power supply rise time	3.01	3.13	3.25	V
			Power supply fall time	2.94	3.06	3.18	V
		VLVD3	Power supply rise time	2.90	3.02	3.14	V
			Power supply fall time	2.85	2.96	3.07	V
		VLVD4	Power supply rise time	2.81	2.92	3.03	V
			Power supply fall time	2.75	2.86	2.97	V
		VLVD5	Power supply rise time	2.70	2.81	2.92	V
			Power supply fall time	2.64	2.75	2.86	V
		VLVD6	Power supply rise time	2.61	2.71	2.81	V
			Power supply fall time	2.55	2.65	2.75	V
		VLVD7	Power supply rise time	2.51	2.61	2.71	V
			Power supply fall time	2.45	2.55	2.65	V
Minimum pu	ulse width	t∟w		300			μS
Detection de	elay time					300	μS

LVD Detection Voltage of Interrupt & Reset Mode

(TA = -40 to +105°C, VPDR \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Cond	Conditions			MAX.	Unit
Interrupt and reset	VLVDD0	VPOC2, VPOC1, VPOC0 = 0, 1, 1,	VPOC2, VPOC1, VPOC0 = 0, 1, 1, falling reset voltage		2.75	2.86	V
mode	VLVDD1	LVIS1, LVIS0 = 1, 0	LVIS1, LVIS0 = 1, 0 Rising release reset voltage		2.92	3.03	V
			Falling interrupt voltage	2.75	2.86	2.97	V
	VLVDD2	LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.90	3.02	3.14	V
			Falling interrupt voltage	2.85	2.96	3.07	V
	Vlvdd3	LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.90	4.06	4.22	V
			Falling interrupt voltage	3.83	3.98	4.13	V



4.3 25-pin Products

R5F1008AALA, R5F1008CALA, R5F1008DALA, R5F1008EALA R5F1018AALA, R5F1018CALA, R5F1018DALA, R5F1018EALA R5F1008AGLA, R5F1008CGLA, R5F1008DGLA, R5F1008EGLA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-WFLGA25-3x3-0.50	PWLG0025KA-A	P25FC-50-2N2-2	0.01



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4.8 44-pin Products

R5F100FAAFP, R5F100FCAFP, R5F100FDAFP, R5F100FEAFP, R5F100FFAFP, R5F100FGAFP, R5F100FHAFP, R5F100FJAFP, R5F100FKAFP, R5F100FLAFP

R5F101FAAFP, R5F101FCAFP, R5F101FDAFP, R5F101FEAFP, R5F101FFAFP, R5F101FGAFP, R5F101FHAFP, R5F101FJAFP, R5F101FKAFP, R5F101FLAFP

R5F100FADFP, R5F100FCDFP, R5F100FDDFP, R5F100FEDFP, R5F100FFDFP, R5F100FGDFP, R5F100FHDFP, R5F100FJDFP, R5F100FKDFP, R5F100FLDFP

R5F101FADFP, R5F101FCDFP, R5F101FDDFP, R5F101FEDFP, R5F101FFDFP, R5F101FGDFP, R5F101FHDFP, R5F101FJDFP, R5F101FKDFP, R5F101FLDFP

R5F100FAGFP, R5F100FCGFP, R5F100FDGFP, R5F100FEGFP, R5F100FFGFP, R5F100FGGFP, R5F100FJGFP

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP44-10x10-0.80	PLQP0044GC-A	P44GB-80-UES-2	0.36



NOTE

Each lead centerline is located within 0.20 mm of its true position at maximum material condition.

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0.10

1.00

1.00

y

ZD

ZE



R5F100PFAFA, R5F100PGAFA, R5F100PHAFA, R5F100PJAFA, R5F100PKAFA, R5F100PLAFA R5F101PFAFA, R5F101PGAFA, R5F101PHAFA, R5F101PJAFA, R5F101PKAFA, R5F101PLAFA R5F100PFDFA, R5F100PGDFA, R5F100PHDFA, R5F100PJDFA, R5F100PKDFA, R5F100PLDFA R5F101PFDFA, R5F101PGDFA, R5F101PHDFA, R5F101PJDFA, R5F101PKDFA, R5F101PLDFA R5F100PFGFA, R5F100PGGFA, R5F100PHGFA, R5F100PJGFA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP100-14x20-0.65	PLQP0100JC-A	P100GF-65-GBN-1	0.92



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0.10

0.575

0.825

y ZD

ZE

Revision History

RL78/G13 Data Sheet

	Description		
Rev.	Date	Page	Summary
1.00	Feb 29, 2012	-	First Edition issued
2.00	Oct 12, 2012	7	Figure 1-1. Part Number, Memory Size, and Package of RL78/G13: Pin count corrected.
		25	1.4 Pin Identification: Description of pins INTP0 to INTP11 corrected.
		40, 42, 44	1.6 Outline of Functions: Descriptions of Subsystem clock, Low-speed on-chip oscillator, and General-purpose register corrected.
		41, 43, 45	1.6 Outline of Functions: Lists of Descriptions changed.
		59, 63, 67	Descriptions of Note 8 in a table corrected.
		68	(4) Common to RL78/G13 all products: Descriptions of Notes corrected.
		69	2.4 AC Characteristics: Symbol of external system clock frequency corrected.
		96 to 98	2.6.1 A/D converter characteristics: Notes of overall error corrected.
		100	2.6.2 Temperature sensor characteristics: Parameter name corrected.
		104	2.8 Flash Memory Programming Characteristics: Incorrect descriptions corrected.
		116	3.10 52-pin products: Package drawings of 52-pin products corrected.
		120	3.12 80-pin products: Package drawings of 80-pin products corrected.
3.00	Aug 02, 2013	1	Modification of 1.1 Features
		3	Modification of 1.2 List of Part Numbers
		4 to 15	Modification of Table 1-1. List of Ordering Part Numbers, note, and caution
		16 to 32	Modification of package type in 1.3.1 to 1.3.14
		33	Modification of description in 1.4 Pin Identification
		48, 50, 52	Modification of caution, table, and note in 1.6 Outline of Functions
		55	Modification of description in table of Absolute Maximum Ratings ($T_A = 25^{\circ}C$)
		57	Modification of table, note, caution, and remark in 2.2.1 X1, XT1 oscillator characteristics
		57	Modification of table in 2.2.2 On-chip oscillator characteristics
		58	Modification of note 3 of table (1/5) in 2.3.1 Pin characteristics
		59	Modification of note 3 of table (2/5) in 2.3.1 Pin characteristics
		63	Modification of table in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products
		64	Modification of notes 1 and 4 in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products
		65	Modification of table in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products
		66	Modification of notes 1, 5, and 6 in (1) Flash ROM: 16 to 64 KB of 20- to 64- pin products
		68	Modification of notes 1 and 4 in (2) Flash ROM: 96 to 256 KB of 30- to 100- pin products
		70	Modification of notes 1, 5, and 6 in (2) Flash ROM: 96 to 256 KB of 30- to 100-pin products
		72	Modification of notes 1 and 4 in (3) Flash ROM: 384 to 512 KB of 44- to 100- pin products
		74	Modification of notes 1, 5, and 6 in (3) Flash ROM: 384 to 512 KB of 44- to 100-pin products
		75	Modification of (4) Peripheral Functions (Common to all products)
		77	Modification of table in 2.4 AC Characteristics
		78, 79	Addition of Minimum Instruction Execution Time during Main System Clock Operation
		80	Modification of figures of AC Timing Test Points and External System Clock Timing

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